

Insulated Gate Bipolar Transistor Trench PT IGBT, 600 V, 250 A

Proprietary Vishay IGBT Silicon “L Series”



SOT-227

PRODUCT SUMMARY	
V_{CES}	600 V
I_C DC ⁽¹⁾	239 A at 90 °C
$V_{CE(on)}$ typical at 100 A, 25 °C	1.10 V
Speed	DC to 1 kHz
Package	SOT-227
Circuit	Single switch no diode

Note

⁽¹⁾ Maximum continuous collector current 100 A to do not exceed the maximum temperature of terminals

FEATURES

- Standard speed Trench PT IGBT
- Fully isolated package
- Very low internal inductance (≤ 5 nH typical)
- Industry standard outline
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



**RoHS
COMPLIANT**

BENEFITS

- Optimized for high current inverter stages (AC TIG welding machine)
- Direct mounting to heatsink
- Plug-in compatible with other SOT-227 packages
- Lower conduction losses
- Low EMI, requires less snubbing

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V_{CES}		600	V
Continuous collector current	I_C	$T_C = 25\text{ °C}$	380	A
		$T_C = 90\text{ °C}$	239	
Pulsed collector current	I_{CM}		600	
Clamped inductive load current	I_{LM}		400	
Gate-to-emitter voltage	V_{GE}		± 20	V
Power dissipation, IGBT	P_D	$T_C = 25\text{ °C}$	893	W
		$T_C = 90\text{ °C}$	429	
Isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	V

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CES)}$	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	600	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 100\text{ A}$	-	1.10	1.30	
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 125\text{ °C}$	-	1.03	-	
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 150\text{ °C}$	-	1.0	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 3.2\text{ mA}$	4.1	6.1	8.1	
		$V_{CE} = V_{GE}, I_C = 3.2\text{ mA}, T_J = 125\text{ °C}$	-	3.5	-	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 3.2\text{ mA}, (25\text{ °C to }125\text{ °C})$	-	-26	-	mV/°C
Collector to emitter leakage current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$	-	1.0	100	μA
		$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 125\text{ °C}$	-	350	-	
		$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 150\text{ °C}$	-	700	-	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 350	nA



SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Total gate charge (turn-on)	Q_g	$I_C = 100\text{ A}, V_{CC} = 400\text{ V}, V_{GE} = 15\text{ V}$		-	942	-	nC		
Gate to emitter charge (turn-on)	Q_{ge}			-	295	-			
Gate to collector charge (turn-on)	Q_{gc}			-	802	-			
Turn-on switching loss	E_{on}	$I_C = 100\text{ A}, V_{CC} = 480\text{ V}, V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C}$		-	2.2	-	mJ		
Turn-off switching loss	E_{off}			-	11	-			
Total switching loss	E_{tot}			-	13.2	-			
Turn-on delay time	$t_{d(on)}$			$I_C = 100\text{ A}, V_{CC} = 480\text{ V}, V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$		-	300	-	ns
Rise time	t_r					-	85	-	
Turn-off delay time	$t_{d(off)}$					-	515	-	
Fall time	t_f	-	450			-			
Turn-on switching loss	E_{on}	-	2.6			-	mJ		
Turn-off switching loss	E_{off}	-	21.5			-			
Total switching loss	E_{tot}	-	24.1	-					
Turn-on delay time	$t_{d(on)}$	$I_C = 100\text{ A}, V_{CC} = 480\text{ V}, V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$		-	285	-	ns		
Rise time	t_r			-	85	-			
Turn-off delay time	$t_{d(off)}$			-	785	-			
Fall time	t_f			-	790	-			
Reverse bias safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 400, R_g = 5\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V}, V_{CC} = 480\text{ V}, V_P = 600\text{ V}, L = 500\text{ }\mu\text{H}$		Fullsquare					

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	T_J, T_{Stg}		-40	-	150	$^\circ\text{C}$
Junction to case	R_{thJC}		-	-	0.14	$^\circ\text{C/W}$
Case to heatsink	R_{thCS}	Flat, greased surface	-	0.1	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf.in)
Case style		SOT-227				

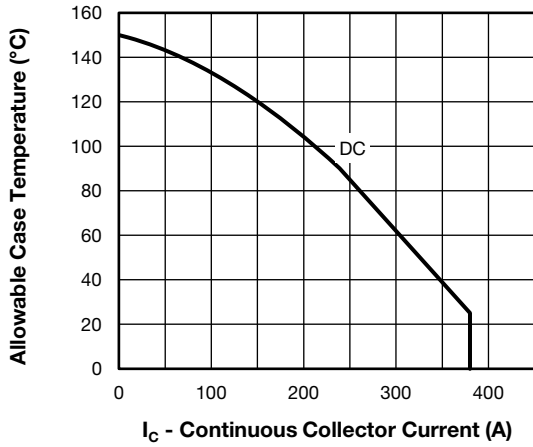


Fig. 1 - Maximum DC IGBT Collector Current vs. Case Temperature

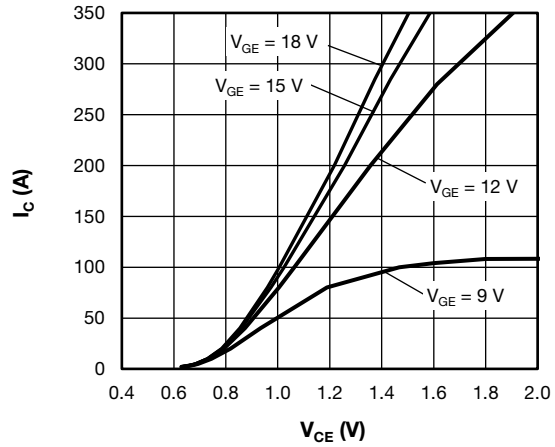


Fig. 4 - Typical Output Characteristics vs. V_{GE} at 125 °C

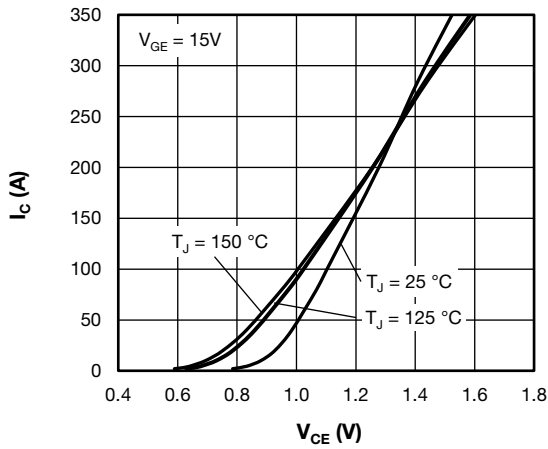


Fig. 2 - Typical IGBT Output Characteristics vs. $V_{GE} = 15 V$

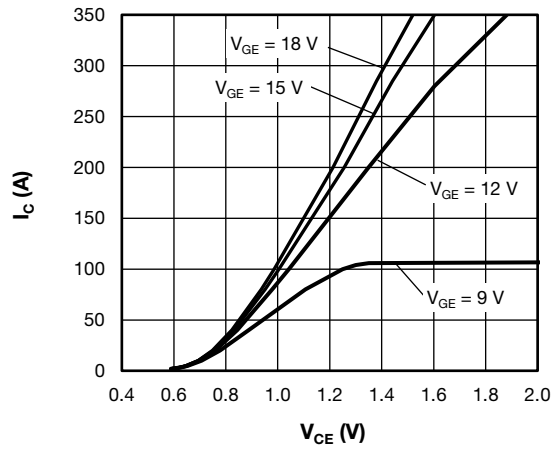


Fig. 5 - Typical Output Characteristics vs. V_{GE} at 150 °C

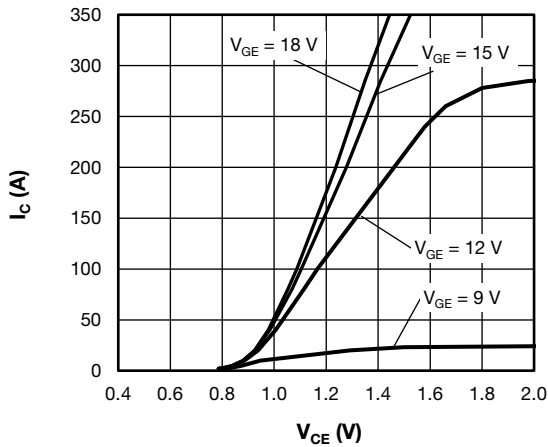


Fig. 3 - Typical Output Characteristics vs. V_{GE} at 25 °C

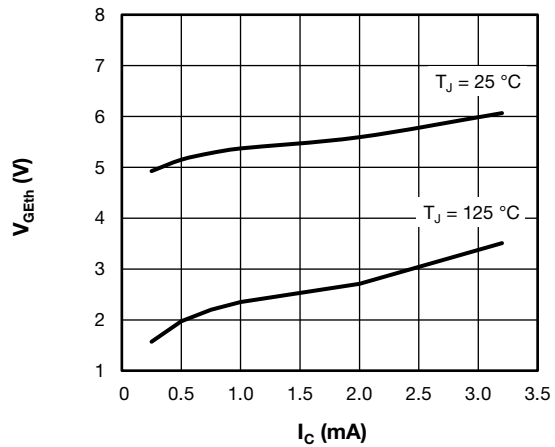


Fig. 6 - Typical Gate Threshold Voltage Characteristics

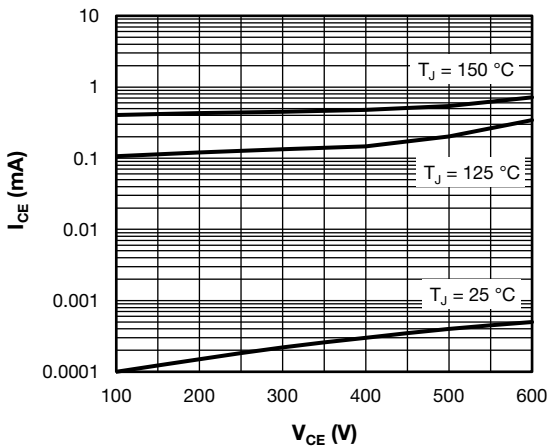


Fig. 7 - Typical Zero Voltage Collector Current

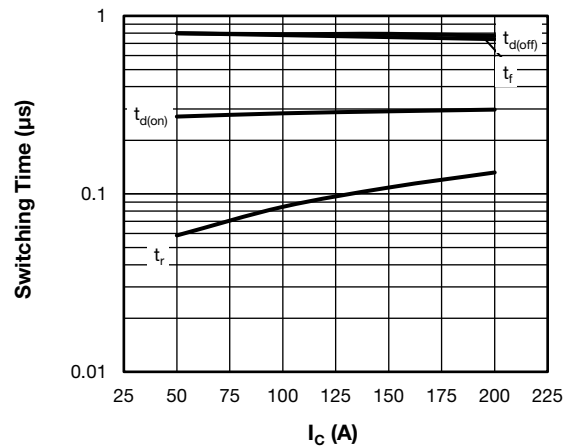


Fig. 10 - Typical IGBT Switching Time vs. I_C
 $T_J = 125\text{ °C}$, $V_{CC} = 480\text{ V}$, $V_{GE} = 15\text{ V}$, $L = 500\text{ μH}$, $R_g = 5\text{ Ω}$
Diode used: 60APH06

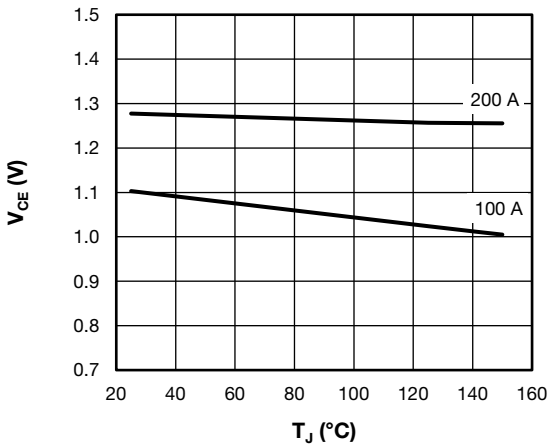


Fig. 8 - Typical V_{CE} vs. Junction Temperature

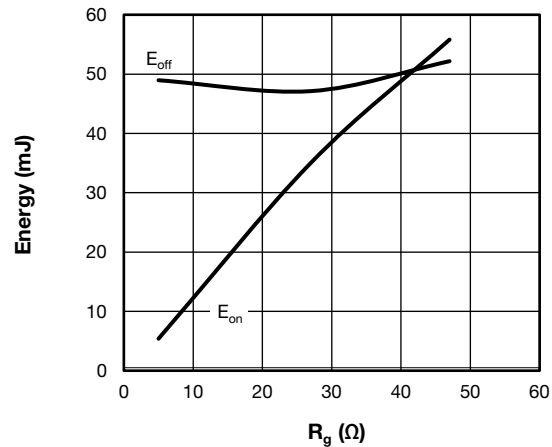


Fig. 11 - Typical IGBT Energy Losses vs. R_g
 $T_J = 125\text{ °C}$, $I_C = 200\text{ A}$, $V_{CC} = 480\text{ V}$, $V_{GE} = 15\text{ V}$, $L = 500\text{ μH}$,
 $R_g = 5\text{ Ω}$, Diode used: 60APH06

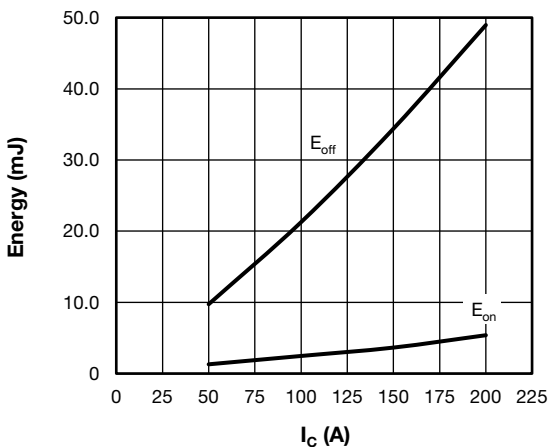


Fig. 9 - Typical IGBT Energy Losses vs. I_C
 $T_J = 125\text{ °C}$, $V_{CC} = 480\text{ V}$, $V_{GE} = 15\text{ V}$, $L = 500\text{ μH}$, $R_g = 5\text{ Ω}$
Diode used: 60APH06

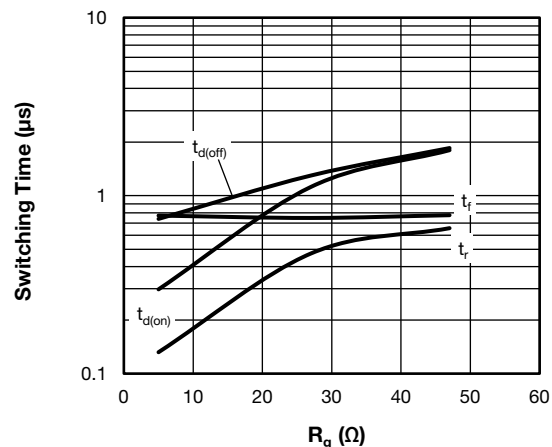


Fig. 12 - Typical IGBT Switching Time vs. R_g
 $T_J = 125\text{ °C}$, $I_C = 200\text{ A}$, $V_{CC} = 480\text{ V}$, $V_{GE} = 15\text{ V}$, $L = 500\text{ μH}$,
 $R_g = 5\text{ Ω}$, Diode used: 60APH06

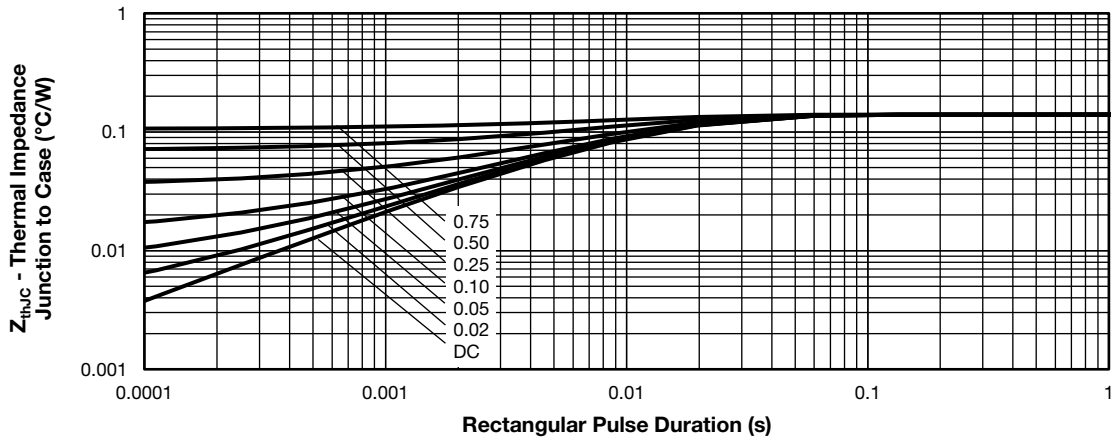


Fig. 13 - Maximum Thermal Impedance Characteristics

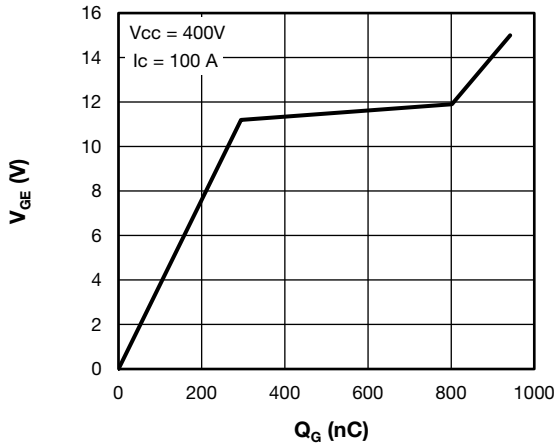
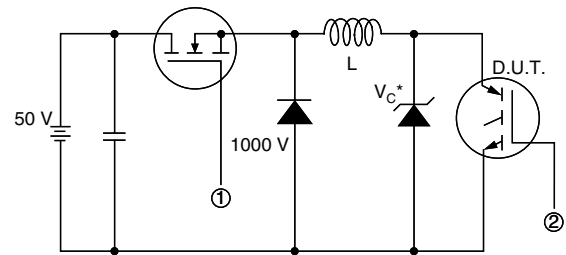


Fig. 14 - Typical Gate Charge vs. Gate Emitter Voltage



* Driver same type as D.U.T.; $V_C = 80\%$ of V_{CE} (max)
Note: Due to the 50 V power supply, pulse width and inductor will increase to obtain rated I_d

Fig. 16a - Clamped Inductive Load Test Circuit

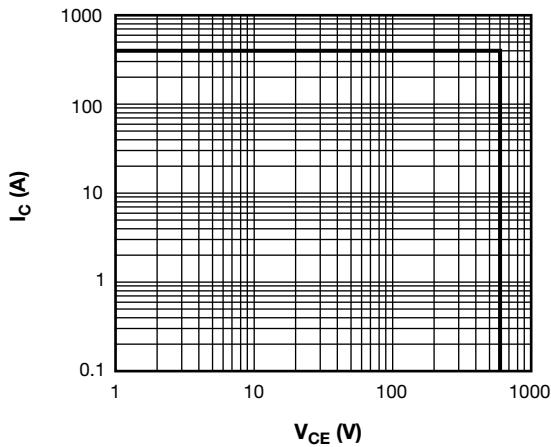


Fig. 15 - Reverse BIAS SOA, $T_J = 150^\circ\text{C}$, $V_{GE} = 15\text{ V}$

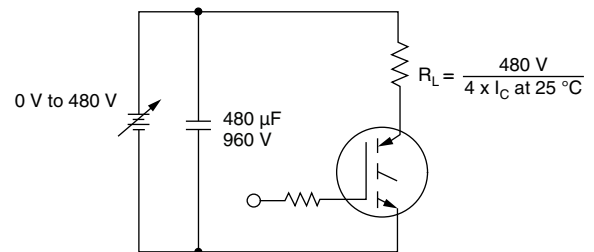
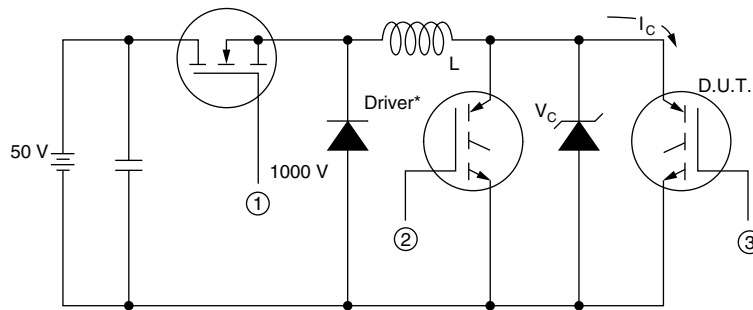


Fig. 16b - Pulsed Collector Current Test Circuit



* Driver same type as D.U.T., $V_C = 480\text{ V}$

Fig. 17a - Switching Lost Test Circuit

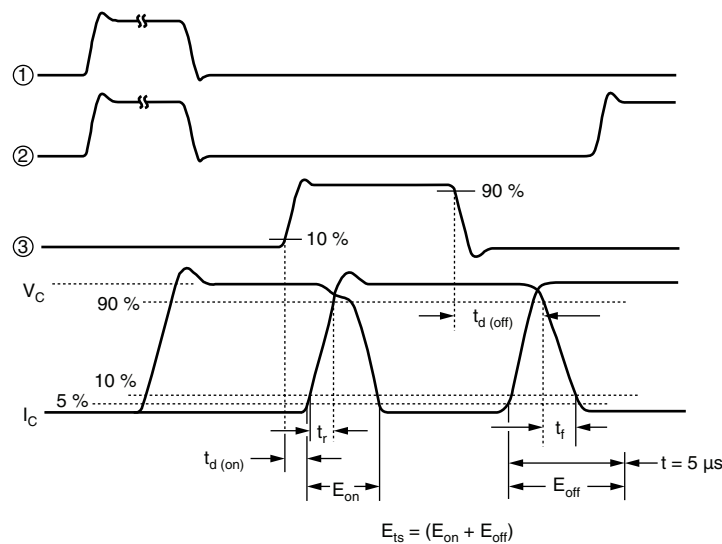


Fig. 17b - Switching Loss Waveforms

ORDERING INFORMATION TABLE

Device code	VS-	G	P	250	S	A	60	S
	①	②	③	④	⑤	⑥	⑦	⑧

- 1** - Vishay Semiconductors product
- 2** - Insulated Gate Bipolar Transistor (IGBT)
- 3** - P = Trench PT IGBT
- 4** - Current rating (250 = 250 A)
- 5** - Circuit configuration (S = single switch, no diode)
- 6** - Package indicator (A = SOT-227)
- 7** - Voltage rating (60 = 600 V)
- 8** - Speed/type (S = standard speed)



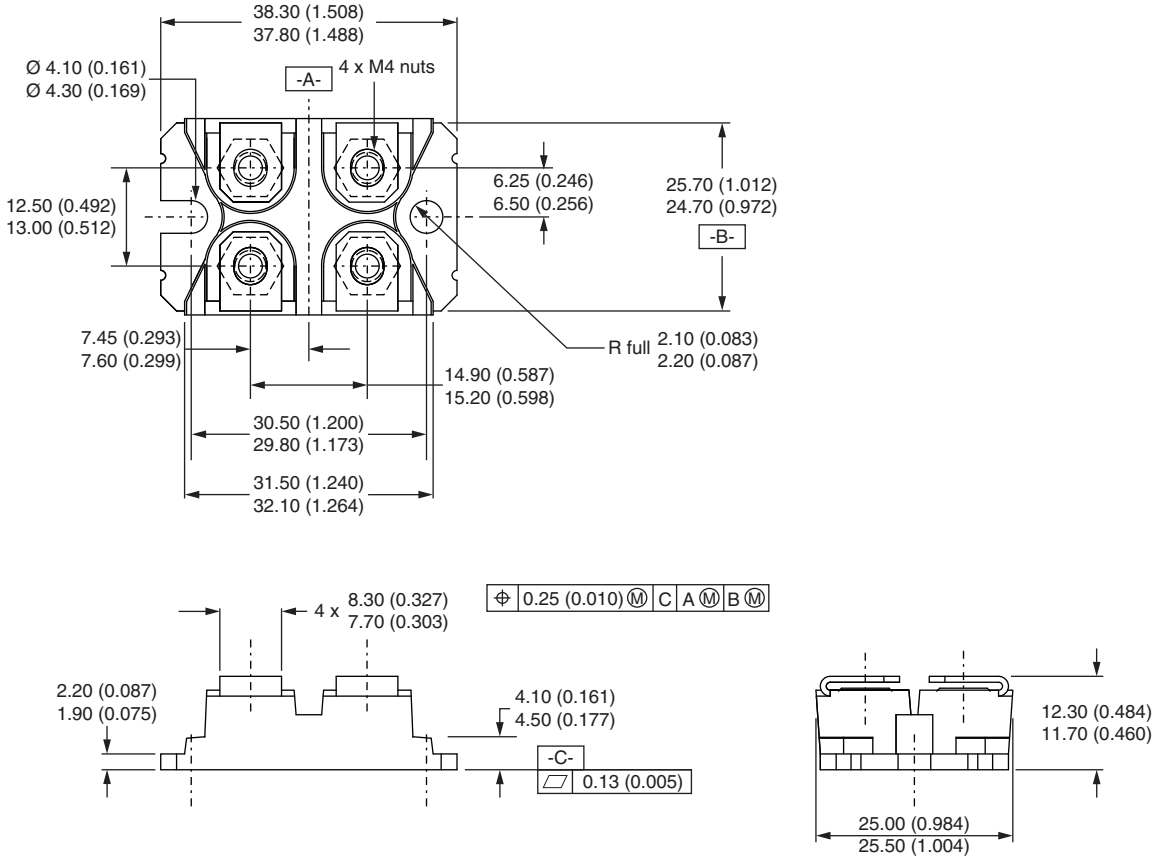
CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Single switch, no diode	S	

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95423
Packaging information	www.vishay.com/doc?95425



SOT-227 Generation II

DIMENSIONS in millimeters (inches)



Note

- Controlling dimension: millimeter



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